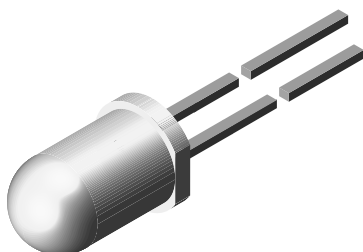


High Power Infrared Emitting Diode, RoHS Compliant, 940 nm, GaAlAs/GaAs



94 8389

DESCRIPTION

TSAL7200 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power molded in a clear, untinted plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): $\varnothing$ 5
- Peak wavelength: $\lambda_p = 940$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 17^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

APPLICATIONS

- Infrared remote control units with high power requirements
- Free air transmission systems
- Infrared source for optical counters and card readers

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSAL7200	60	± 17	940	800

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSAL7200	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100$ μ s	I_{FM}	200	mA
Surge forward current	$t_p = 100$ μ s	I_{FSM}	1.5	A
Power dissipation		P_V	160	mW
Junction temperature		T_j	100	$^\circ$ C
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ$ C
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ$ C
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ$ C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R_{thJA}	230	K/W

Note

$T_{amb} = 25$ $^\circ$ C, unless otherwise specified

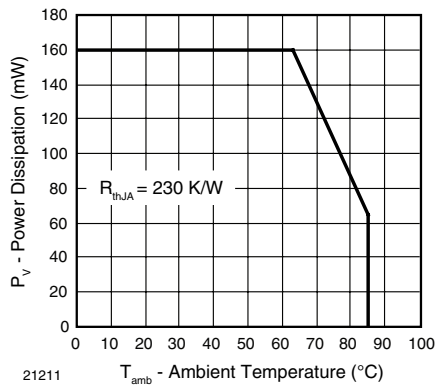


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

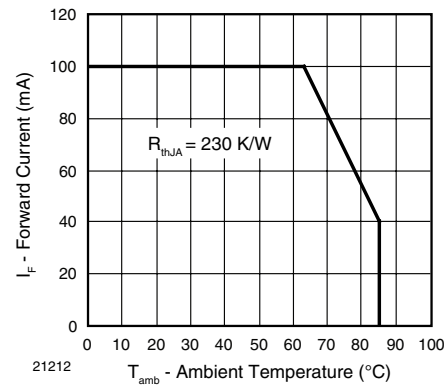
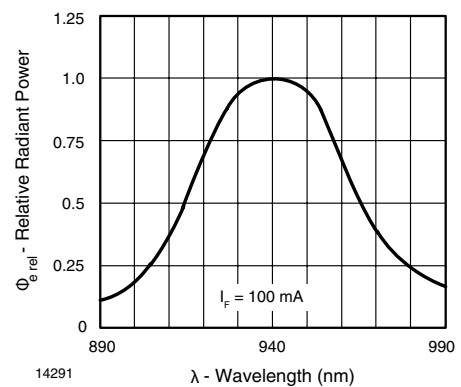
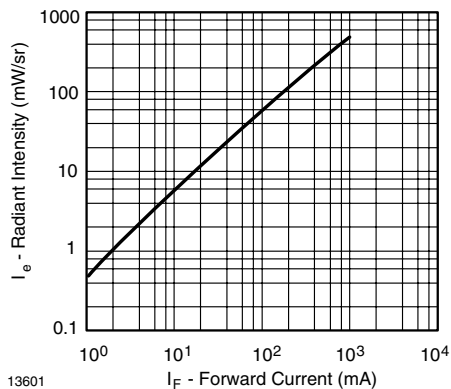
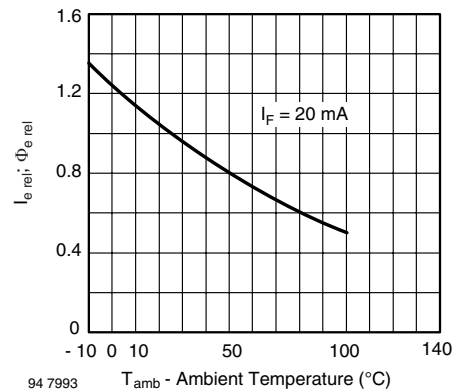
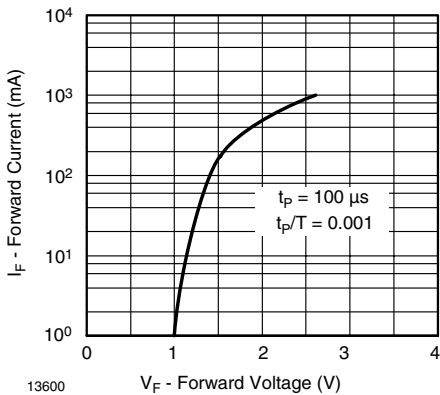
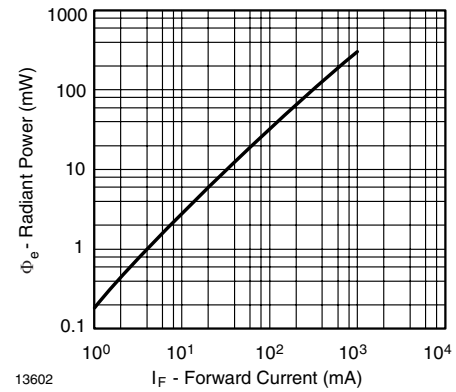
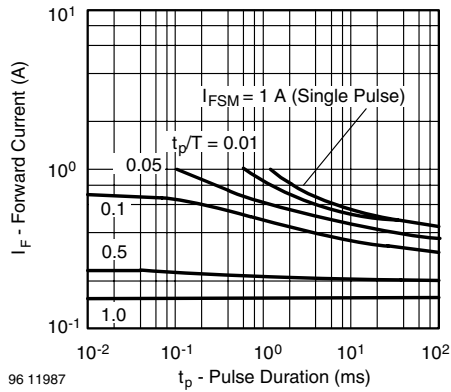


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	V_F		1.35	1.6	V
	$I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$	V_F		2.6	3	V
Temperature coefficient of V_F	$I_F = 1 \text{ mA}$	TK_{VF}		- 1.8		mV/K
Reverse current	$V_R = 5 \text{ V}$	I_R			10	μA
Junction capacitance	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, $E = 0$	C_j		25		pF
Radiant intensity	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	I_e	40	60	200	mW/sr
	$I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$	I_e	340	500		mW/sr
Radiant power	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	ϕ_e		35		mW
Temperature coefficient of ϕ_e	$I_F = 20 \text{ mA}$	TK_{ϕ_e}		- 0.6		%/K
Angle of half intensity		φ		± 17		deg
Peak wavelength	$I_F = 100 \text{ mA}$	λ_p		940		nm
Spectral bandwidth	$I_F = 100 \text{ mA}$	$\Delta\lambda$		50		nm
Temperature coefficient of λ_p	$I_F = 100 \text{ mA}$	TK_{λ_p}		0.2		nm/K
Rise time	$I_F = 100 \text{ mA}$	t_r		800		ns
Fall time	$I_F = 100 \text{ mA}$	t_f		800		ns
Virtual source diameter	Method: 63 % encircled energy	d		2.4		mm

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

**BASIC CHARACTERISTICS** $T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified



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